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### Encapsulation for transition metal dichalcogenide nanosheet transistor and methods of fabrication

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#### Abstract

A transistor includes a channel layer including a transition metal dichalcogenide (TMD) material, an encapsulation layer on a first portion of the channel layer, a gate electrode above the encapsulation layer, a gate dielectric layer between the gate electrode and the encapsulation layer. The transistor further includes a source contact on a second portion of the channel layer and a drain contact on a third portion of the channel layer, where the gate structure is between drain contact and the source contact.

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## Background/Summary

## BACKGROUND

(1) Scaling of features in integrated circuit structures has been a driving force behind an ever-growing semiconductor industry. Scaling to smaller and smaller transistors enables increased densities of functional units on limited real estate of semiconductor chips. Scaling of such transistors, which include silicon channels, becomes more challenging when device metrics such as mobility, subthreshold slope or gate capacitance, for example, become adversely affected at dimensions less than 5 nm. Non-silicon based channel materials that include transition metal dichalcogenide (TMD) have emerged as viable alternatives for implementation as transistor channels. However, fabrication of N-type TMD transistor and P-type TMD transistor on a same substrate continues to be challenging.

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## Description

### BRIEF DESCRIPTION OF THE DRAWINGS

- (1) The material described herein is illustrated by way of example and not by way of limitation in the accompanying figures. For simplicity and clarity of illustration, elements illustrated in the figures are not necessarily drawn to scale. For example, the dimensions of some elements may be exaggerated relative to other elements for clarity. Also, various physical features may be represented in their simplified “ideal” forms and geometries for clarity of discussion, but it is nevertheless to be understood that practical implementations may only approximate the illustrated ideals. For example, smooth surfaces and square intersections may be drawn in disregard of finite roughness, corner-rounding, and imperfect angular intersections characteristic of structures formed by nanofabrication techniques. Further, where considered appropriate, reference labels have been repeated among the figures to indicate corresponding or analogous elements.
- (2) FIG. 1A is a cross-sectional illustration of a transistor including an encapsulation layer, in accordance with an embodiment of the present disclosure.
- (3) FIG. 1B is a schematic of a monolayer of TMD material.
- (4) FIG. 1C is a cross-sectional illustration of a pair of N and P type TMD transistors, in accordance with an embodiment of the present disclosure.
- (5) FIG. 1D is a cross-sectional illustration of a pair of N and P type TMD transistors, in accordance with an embodiment of the present disclosure.
- (6) FIG. 2A is cross-sectional illustration of a transistor including a first TMD channel and second TMD channel above the first TMD channel and an encapsulation layer adjacent to each TMD channel in accordance with an embodiment of the present disclosure.
- (7) FIG. 2B is a cross-sectional illustration along the line A-A' of the structure in FIG. 2A, where the encapsulation layer clads the TMD channels and a gate dielectric clads the encapsulation layer, and the gate electrode clads the gate dielectric layer.
- (8) FIG. 2C is a cross-sectional illustration of a pair of N and P type TMD transistors, in accordance with an embodiment of the present disclosure.
- (9) FIG. 2D is a cross-sectional illustration of a pair of N and P type TMD transistors, in accordance with an embodiment of the present disclosure.
- (10) FIG. 3 is a method to fabricate a transistor depicted in FIG. 2A, in accordance with an embodiment of the present disclosure.
- (11) FIG. 4A is a cross-sectional illustration of material layer stack for fabrication of a TMD transistor device, where the material layer stack includes a plurality of bilayers of a TMD layer on a sacrificial layer, in accordance with an embodiment of the present disclosure.
- (12) FIG. 4B is a cross sectional illustration of a block formed by patterning the material layer stack.

- (13) FIG. 5A illustrates the structure of FIG. 5B following the formation of a dielectric on the block and following the formation of a mask to form an opening adjacent to portions of sidewalls of the block.
- (14) FIG. 5B is a plan-view illustration of the structure in FIG. 5A.
- (15) FIG. 6A is a cross-sectional illustration of a plurality of TMD channel layers formed after etching the dielectric, exposing sidewalls of the block, and selectively removing the sacrificial III-N material.
- (16) FIG. 6B is a plan-view illustration of the structure in FIG. 6A.
- (17) FIG. 7A is a cross-sectional illustration of the process to form an encapsulation layer on each of the TMD channel layers.
- (18) FIG. 7B is a cross-sectional illustration along a line A-A' through the structure in FIG. 7A.
- (19) FIG. 8 is a cross-sectional illustration of a pair of partially fabricated devices structures that are laterally spaced apart by a dielectric.
- (20) FIG. 9A is a cross-sectional illustration of the structure in FIG. 7A following the formation of a dummy gate structure in the opening and following the deposition of a dielectric adjacent to the dummy gate structure.
- (21) FIG. 9B illustrates the structure of FIG. 9A following the removal of the dummy gate structure.
- (22) FIG. 10A illustrates the structure of FIG. 10B following the formation of a gate structure in the opening.
- (23) FIG. 10B is a cross sectional illustration through a line A-A' in FIG. 10A.
- (24) FIG. 11A is a cross-sectional illustration of the structure in FIG. 10A following the formation of an opening for depositing source contact material on one end of a plurality of TMD channel layers and an opening for depositing a drain contact material on a second end of the plurality of TMD channel layers, in accordance with an embodiment of the present disclosure.
- (25) FIG. 11B is an enhanced cross-sectional illustration of a top portion of a TMD channel layer.
- (26) FIG. 12 is a cross-sectional illustration of the structure in FIG. 11A following the formation of a source contact on one end of a plurality of TMD channel layers and a drain contact on a second end of the plurality of TMD channel layers, in accordance with an embodiment of the present disclosure.
- (27) FIG. 13 is a cross-sectional illustration of a transistor adjacent to a partially fabricated transistor structure laterally separated by a dielectric.
- (28) FIG. 14A is a cross-sectional illustration of a memory device coupled with a transistor including a plurality of TMD channels, in accordance with an embodiment of the present disclosure.
- (29) FIG. 14B is a cross-sectional illustration of a magnetic tunnel junction device, in accordance with an embodiment of the present disclosure.
- (30) FIG. 14C is a cross-sectional illustration of a resistive random-access memory device, in accordance with an embodiment of the present disclosure.
- (31) FIG. 15 illustrates a computing device in accordance with embodiments of the present disclosure.
- (32) FIG. 16 illustrates an integrated circuit (IC) structure that includes one or more embodiments of the present disclosure.

#### DESCRIPTION OF THE EMBODIMENTS

(33) Encapsulation for TMD nanosheet transistors and methods of fabrication are described. In the following description, numerous specific details are set forth, such as structural schemes and detailed fabrication methods in order to provide a thorough understanding of embodiments of the present disclosure. It will be apparent to one skilled in the art that embodiments of the present disclosure may be practiced without these specific details. In other instances, well-known features, such as operations associated with TMD nanosheet transistor, are described in lesser detail in order

to not unnecessarily obscure embodiments of the present disclosure. Furthermore, it is to be understood that the various embodiments shown in the Figures are illustrative representations and are not necessarily drawn to scale.

(34) In some instances, in the following description, well-known methods and devices are shown in block diagram form, rather than in detail, to avoid obscuring the present disclosure. Reference throughout this specification to “an embodiment” or “one embodiment” or “some embodiments” means that a particular feature, structure, function, or characteristic described in connection with the embodiment is included in at least one embodiment of the disclosure. Thus, the appearances of the phrase “in an embodiment” or “in one embodiment” or “some embodiments” in various places throughout this specification are not necessarily referring to the same embodiment of the disclosure. Furthermore, the particular features, structures, functions, or characteristics may be combined in any suitable manner in one or more embodiments. For example, a first embodiment may be combined with a second embodiment anywhere the particular features, structures, functions, or characteristics associated with the two embodiments are not mutually exclusive.

(35) As used in the description and the appended claims, the singular forms “a,” “an” and “the” are intended to include the plural forms as well, unless the context clearly indicates otherwise. It will also be understood that the term “and/or” as used herein refers to and encompasses any and all possible combinations of one or more of the associated listed items.

(36) The terms “coupled” and “connected,” along with their derivatives, may be used herein to describe functional or structural relationships between components. It should be understood that these terms are not intended as synonyms for each other. Rather, in particular embodiments, “connected” may be used to indicate that two or more elements are in direct physical, optical, or electrical contact with each other. “Coupled” may be used to indicate that two or more elements are in either direct or indirect (with other intervening elements between them) physical, electrical or in magnetic contact with each other, and/or that the two or more elements co-operate or interact with each other (e.g., as in a cause and effect relationship).

(37) The terms “over,” “under,” “between,” and “on” as used herein refer to a relative position of one component or material with respect to other components or materials where such physical relationships are noteworthy. For example, in the context of materials, one material or material disposed over or under another may be directly in contact or may have one or more intervening materials. Moreover, one material disposed between two materials may be directly in contact with the two layers or may have one or more intervening layers. In contrast, a first material “on” a second material is in direct contact with that second material/material. Similar distinctions are to be made in the context of component assemblies. As used throughout this description, and in the claims, a list of items joined by the term “at least one of” or “one or more of” can mean any combination of the listed terms.

(38) The term “adjacent” here generally refers to a position of a thing being next to (e.g., immediately next to or close to with one or more things between them) or adjoining another thing (e.g., abutting it).

(39) The term “signal” may refer to at least one current signal, voltage signal, magnetic signal, or data/clock signal. The meaning of “a,” “an,” and “the” include plural references. The meaning of “in” includes “in” and “on.”

(40) The term “device” may generally refer to an apparatus according to the context of the usage of that term. For example, a device may refer to a stack of layers or structures, a single structure or layer, a connection of various structures having active and/or passive elements, etc. Generally, a device is a three-dimensional structure with a plane along the x-y direction and a height along the z direction of an x-y-z Cartesian coordinate system. The plane of the device may also be the plane of an apparatus which comprises the device.

(41) As used throughout this description, and in the claims, a list of items joined by the term “at least one of” or “one or more of” can mean any combination of the listed terms.

(42) Unless otherwise specified in the explicit context of their use, the terms “substantially equal,” “about equal” and “approximately equal” mean that there is no more than incidental variation between two things so described. In the art, such variation is typically no more than  $\pm 10\%$  of a predetermined target value.

(43) The terms “left,” “right,” “front,” “back,” “top,” “bottom,” “over,” “under,” and the like in the description and in the claims, if any, are used for descriptive purposes and not necessarily for describing permanent relative positions. For example, the terms “over,” “under,” “front side,” “back side,” “top,” “bottom,” “over,” “under,” and “on” as used herein refer to a relative position of one component, structure, or material with respect to other referenced components, structures or materials within a device, where such physical relationships are noteworthy. These terms are employed herein for descriptive purposes only and predominantly within the context of a device z-axis and therefore may be relative to an orientation of a device. Hence, a first material “over” a second material in the context of a figure provided herein may also be “under” the second material if the device is oriented upside-down relative to the context of the figure provided. In the context of materials, one material disposed over or under another may be directly in contact or may have one or more intervening materials. Moreover, one material disposed between two materials may be directly in contact with the two layers or may have one or more intervening layers. In contrast, a first material “on” a second material is in direct contact with that second material. Similar distinctions are to be made in the context of component assemblies.

(44) The term “between” may be employed in the context of the z-axis, x-axis or y-axis of a device. A material that is between two other materials may be in contact with one or both of those materials, or it may be separated from both of the other two materials by one or more intervening materials. A material “between” two other materials may therefore be in contact with either of the other two materials, or it may be coupled to the other two materials through an intervening material. A device that is between two other devices may be directly connected to one or both of those devices, or it may be separated from both of the other two devices by one or more intervening devices.

(45) To enable feature size scaling in silicon channels, transistor architecture including nanowire and stacked nanowires have been adopted. Nanowire transistors provide benefits such as near ideal sub-threshold slopes, low leakage current and less degradation of mobility with gate voltage compared to other transistor architectures. Stacked nanowires can advantageously increase drive current in a transistors. As dimensions of various components of nanowire transistors (channel width and gate length) are decreased to increase device density, device metrics such as carrier mobility and subthreshold slope, parasitic capacitance, may be adversely impacted. Nanowire transistors that include monocrystalline silicon channels, in particular, are prone to mobility and subthreshold slope degradation as channel widths approach 7 nm. Mobility in silicon nanowires diminishes by over 60% as nanowires are scaled below 7 nm to 3.5 nm, for example. Mobility degradation may be attributed to impurity scattering loss in silicon channels.

(46) Transistors fashioned from two dimensional materials, such as transition metal dichalcogenide (TMD), offer several advantages over conventional silicon. In such implementation, TMD nanosheets can be implemented as a channel layer. A monolayer of a TMD material may be on the order of 0.7 nm, or inherently 2-dimensional (2D). TMD materials have a high Young's modulus and can be utilized to form 2-d nanosheets. In some embodiments, the plurality of nanosheets may be stacked to provide channel layers for a TMD nanosheet transistor.

(47) While nanosheet transistors fashioned from TMD materials offer transistor performance benefits, doping of TMD channel layers to fabricate an N-type or P-type FET is challenging. Transistors fabricated from most semiconducting TMD materials heavily favor N-type over P-type behavior. The N-type behavior arises from chalcogen vacancies in TMD materials. Examples of TMD materials that exhibit N-type behavior include sulfides of Mo, W, Cr or Ti. Examples of TMD materials that exhibit P-type includes, for example,  $\text{WSe}_2$  or  $\text{WSe}_2$  doped with Ta.

Typically, P-type behavior in transistors utilizing TMD materials are obtained by work function engineering of the gate or the source-drain contact region.

(48) In stacked nanosheet architecture, layers of TMD material are formed part of a material layer stack, where individual layers of TMD material are sandwiched between sacrificial materials. The sacrificial materials are removed to release layers of TMD material for fabrication of transistors. Fabrication of an N-type or a P-type transistor can be chosen based on a type of TMD material. However, integrating different TMD materials on a single plane for a complimentary N and P type transistor is challenging.

(49) The inventors have found that by encapsulating the TMD channel material with a liner (an encapsulation layer) that can modulate threshold voltage,  $V_{sub.T}$ , of a transistor, a single TMD channel material can be advantageously utilized to co-fabricate an N-type adjacent to a P-type FET device. The encapsulation layer is designed to attract electrons from or donate electrons to the TMD channel material. Attracting electrons from the TMD channel material may introduce shallow acceptor states close to the valence band edge of the TMD channel material creating a p-type doping effect. Donating electrons to TMD channel material from encapsulation layer may introduce shallow donor states close to a conduction band edge, leading to a p-type doping effect. In embodiments, electron donor and acceptor levels may be controlled by changing the level of defects in the encapsulation layer. The defects in the encapsulation layer act as centers for charge carrier and depending on the material can provide both positive and negative charge carriers.

(50) In embodiments, because the encapsulation layer can be deposited or grown after forming suspended TMD channel layers, N and P type FETs can be co-fabricated. In one example, an N and a P device may be co-fabricated until a process operation to release the stacked nanosheets after which point, an N or a P region may be masked for further fabrication of P or an N type transistor. This may be followed by masking of the P or the N region to fabricate the N or the P type transistor.

(51) In exemplary embodiments, the encapsulation layer includes a material that has interstitials. The number of defects can be controlled during deposition. Interstitials can result in charge centers in the encapsulation layer and each interstitial site can advantageously donate charge carriers to the TMD channel material. The interstitials may exist in various charged states depending on a material of the charge transfer layer. The charge carriers can be of both negative and positive polarity and may facilitate fabrication of both N-FET and a P-FET devices depending on a material of the encapsulation layer.

(52) In accordance with an embodiment of the present disclosure a transistor includes a channel including a transition metal dichalcogenide (TMD) material, an encapsulation layer on a first portion of the channel, a gate electrode above the encapsulation layer and a gate dielectric layer between the gate electrode and the encapsulation layer. The transistor may be an N-type or a P-type depending on a choice of TMD channel material as well as on the material of the encapsulation layer. The transistor further includes a source contact on a second portion of the channel layer and a drain contact on a third portion of the channel layer, where the gate electrode is between drain contact and the source contact.

(53) Because the choice of TMD channel material and encapsulation can influence a transistor to be a P or an N-type, integration of N and P-type transistor can be advantageously facilitated on a same plane of a substrate using a single channel material. In exemplary embodiments, the N-type and P-type transistors are laterally spaced apart by a dielectric. In one embodiment, for a given TMD channel material, an N-type transistor may include an encapsulation layer, while the same encapsulation layer may be absent in a P-type counterpart or vice versa. In a second embodiment, for a given TMD channel material, an N-type transistor may include a first encapsulation layer and the P-type transistor may include a second encapsulation layer. In embodiments, the TMD channel material and the encapsulation layer may be integrated into a planar transistor or a stacked nanosheet transistor architecture.

(54) FIG. 1A is a cross-sectional illustration of a transistor **100**. The transistor **100** may have a planar or non-planar geometry. In the illustrative embodiment, the transistor **100** has a planar geometry. In an embodiment, the transistor **100** includes a channel layer **102** including a transition metal dichalcogenide (TMD) material (herein TMD channel layer **102**), an encapsulation layer **104** on a portion **102A** of the TMD channel layer **102**. The encapsulation layer **104** includes a material that can facilitate charge transfer between the TMD channel layer **102** and the encapsulation layer **104** to influence an FET characteristic of the transistor **100**, for example N-FET or P-FET. As such, the transistor **100** further includes an insulator such as a gate dielectric layer **106** between the encapsulation layer **104** and a gate electrode **108**. The transistor further includes a source contact **110** on a portion **102B** of the TMD channel layer **102** and a drain contact **112** on a portion **102C** of the TMD channel layer **102**.

(55) FIG. 1B is a schematic of a monolayer of TMD material. In the illustrative embodiment, the TMD material includes a layer of a transition metal **115** between a layer of chalcogen atoms **117A** and a layer of chalcogen atoms **117B**, as shown. Depending on arrangements of the atoms, the TMDs can have various crystal orientations, such as trigonal prismatic (hexagonal), octahedral (tetragonal, T) or their distorted phase (TO). In the illustrative embodiment, the TMD material is hexagonal. The monolayer of TMD (TMD nanosheet), as shown has a thickness of approximately 0.7 nm. The transition metal **115** includes molybdenum, tungsten, titanium or chromium, and the chalcogen atom **117A** and **117B** include one of sulfur, selenium or tellurium. TMD materials described above advantageously provide channel mobility as high as  $700 \text{ cm}^2/\text{Vs}$ .

(56) Referring again to FIG. 1A, the encapsulation layer **104** is a layer that can transfer charge to and from the TMD channel layer **102**. The encapsulation layer **104** is designed to attract electrons from or donate electrons to the TMD channel layer **102**. Polarity of charge and the magnitude of the charges depends on the material of the encapsulation layer **104**. Attracting electrons from the encapsulation layer **104** may introduce shallow acceptor states close to the valence band edge of the TMD channel layer **102** creating a P-type doping effect. Donating electrons to TMD channel layer **102** from encapsulation layer **104** may introduce shallow donor states close to a conduction band edge, leading to N-type doping effect.

(57) In some embodiments, the encapsulation layer **104** further includes interstitials to facilitate charge transfer. In embodiments, the electron donor and acceptor levels may be controlled by changing the number of defects in the encapsulation layer **104**. The number of defects may be controlled, for example, during deposition. Interstitials can result in charge centers in the encapsulation layer **104** and each interstitial site can advantageously accept or donate charge carriers to the TMD channel layer **102**. In an embodiment, the number of defect sites is greater than  $1 \times 10^{18}$  in the encapsulation layer **104**. The interstitials may exist in various charged states depending on a material of the encapsulation layer **104**. The charge carriers can be of both negative and positive polarity, thus facilitating fabrication of both N-FET and a P-FET devices.

(58) However, it is to be appreciated that TMD channel layer may transfer electrons to the encapsulation layer **104** even if no significant defects are present in the encapsulation layer **104**. The encapsulation layer **104** may be lattice matched with the TMD channel layer **102** to obtain band alignment between TMD channel layer **102** and the material of the encapsulation layer **104**. Band alignment may promote transfer of charge between the encapsulation layer **104** and TMD material.

(59) In embodiments the encapsulation layer **104** includes oxygen and at least one of aluminum, molybdenum or tungsten for example aluminum oxide, tungsten oxide, or molybdenum oxide. For a given TMD material, the material of the encapsulation layer **104** may be chosen to form an N-type FET or a P-type FET. In exemplary embodiments, tungsten oxide and molybdenum oxide favors P-type FET and aluminum oxide favors an N-type FET. In some embodiments, the encapsulation layer **104** is a sub-stoichiometric oxide of aluminum, tungsten or molybdenum



aluminum oxide, tungsten oxide, or molybdenum oxide. A sub stoichiometric material may facilitate vacancy migration in the encapsulation layer **104**. In some embodiments, the encapsulation layer **104** includes a metal that is different from a metal of the TMD channel layer **102**. In other examples, the encapsulation layer **104** and the TMD channel layer **102** include a same metal.

(60) In some embodiments, the TMD channel layer **102** may be intrinsically an N-type or a P-type semiconducting TMD. Examples of TMD channel layer **102** that exhibit P-type behavior include WSe.sub.2, or WSe.sub.2 doped with Ta. Examples of TMD channel material that exhibit N-type behavior include sulfides of Mo, W, Ti.

(61) As the encapsulation layer **104** is designed to be a charge transfer layer, the encapsulation layer **104** includes a material that maybe different from a material of the gate dielectric layer **108**. In embodiments, the gate dielectric layer **106** thickness between 1 nm and 4 nm. In embodiments, the encapsulation layer **104** has a thickness between 1 nm and 4 nm.

(62) FIG. 1C is a cross-sectional illustration of a pair of transistors including transistor **100A** adjacent to transistor **100B**, above a shared substrate **101**. The transistors **100A** and **100B** may each have a planar or non-planar geometry. In the illustrative embodiment, each of the transistors **100A** and **100B** have a planar geometry. In the illustrative embodiment, transistor **100A** is the same as transistor **100**. In an embodiment, transistor **100A** is an N-FET and transistor **100B** is a P-FET. In other embodiments, transistor **100A** is a P-FET and the transistor **100B** is an N-FET. As shown, transistor **100B** includes TMD channel layer **102**, and a gate dielectric layer **116** on a portion **102D** of the channel layer **102**, between TMD channel layer **102** and gate electrode **118**. The transistor **100B** further includes a source contact **120** on a portion **102E** of the TMD channel layer **102** and a drain contact **122** on a portion **102F** of the TMD channel layer **102**.

(63) In an exemplary embodiment, transistor **100B** has substantially the same features as transistor **100A**, except that the transistor **100B** includes no encapsulation layer. In one such exemplary embodiment, transistor **100A** includes an Al.sub.2O.sub.3-encapsulation layer **104** and a WSe.sub.2 TMD channel layer **102**. In one such embodiment, transistor **100A** exhibits N-FET behavior. In some such embodiment, transistor **100B** with the WSe.sub.2-TMD channel layer **102** exhibits a P-FET behavior due of an absence of the Al.sub.2O.sub.3-encapsulation layer **104**.

(64) In some embodiments, gate electrode **118** of transistor **100B** includes a different material than a material of the gate electrode **108** of transistor **100A**. Differences in gate electrode may be implemented to advantageously tune threshold voltage for respective N and P transistors.

(65) Examples of gate electrode **108** include a metal such as ruthenium, palladium, platinum, cobalt, nickel, hafnium, zirconium, titanium, tantalum, aluminum, alloys of these metals, and nitrides or carbides of ruthenium, palladium, platinum, cobalt, nickel, hafnium, zirconium, titanium, tantalum, aluminum such as hafnium nitride, zirconium nitride, titanium nitride, tantalum nitride, and aluminum nitride, hafnium carbide, zirconium carbide, titanium carbide, tantalum carbide or aluminum carbide. Examples of gate electrode **118** include a metal such as ruthenium, palladium, platinum, cobalt, nickel, hafnium, zirconium, titanium, tantalum, aluminum, alloys of these metals, and nitrides or carbides of ruthenium, palladium, platinum, cobalt, nickel, hafnium, zirconium, titanium, tantalum, aluminum such as hafnium nitride, zirconium nitride, titanium nitride, tantalum nitride, and aluminum nitride, hafnium carbide, zirconium carbide, titanium carbide, tantalum carbide or aluminum carbide.

(66) In some embodiments the gate dielectric layer **106** and gate dielectric layer **116** may be different. In an embodiment, the gate dielectric layers **106** or **116** each independently include hafnium oxide, hafnium silicon oxide, lanthanum oxide, lanthanum aluminum oxide, zirconium oxide, zirconium silicon oxide, tantalum oxide, titanium oxide, barium strontium titanium oxide, barium titanium oxide, strontium titanium oxide, yttrium oxide, lead scandium tantalum oxide or lead zinc niobate. In embodiments the gate dielectric layer **106** has a thickness between 0.8 nm and 4 nm.

(67) In embodiments, the source contact **110** and drain contact **112** each include a same material. In some embodiments the source contact **120** and drain contact **122** each include a same material. In some embodiments, the source contact **110**, drain contact **112**, source contact **120** and drain contact **122** all include a same material.

(68) In some embodiments, an N and a P type transistor may both include an encapsulation layer. FIG. **1D** is a cross-sectional illustration of a pair of transistors **100A** and **100C**. In an embodiment, transistor **100C** is substantially the same as transistor **100B** with an inclusion of an encapsulation layer **126**. In the illustrative embodiment, transistor **100C** includes an encapsulation layer **126** between the gate electrode **118** and the gate dielectric layer **116**, over the channel portion **102D**. In embodiments, encapsulation layer **126** includes a different material from the material of the encapsulation layer **104**. In exemplary embodiments, the encapsulation layer **126** introduce either shallow acceptor states or shallow donor states to TMD channel layer **102**. In some such embodiments, encapsulation layer **126** introduces either shallow donor states or shallow acceptor states to TMD channel layer **102**, producing an opposite effect of encapsulation layer **104**.

(69) In some examples, the encapsulation layer **104** includes oxygen and aluminum, or sub-stoichiometric aluminum oxide, and the encapsulation layer **126** includes oxygen and molybdenum or tungsten, or sub-stoichiometric tungsten oxide or molybdenum oxide, or vice versa.

(70) In further specific examples, the TMD layer **102** includes sulfides of molybdenum, tungsten, titanium or chromium. In some such embodiments, the encapsulation layer **104** includes oxygen and aluminum, or sub-stoichiometric aluminum oxide, and the encapsulation layer **126** includes oxygen and molybdenum or tungsten, or sub-stoichiometric tungsten oxide or molybdenum oxide, or vice versa. One exemplary embodiment, TMD channel layer **102** includes WS.sub.2 and encapsulation layer **104** includes aluminum oxide and the encapsulation layer **126** includes tungsten oxide.

(71) Referring again to FIG. **1A**, in an embodiment, the source contact **110** includes a barrier layer and a fill metal confined within the barrier layer. In some examples, the barrier layer includes a material such as tantalum nitride or ruthenium. In some examples, the fill metal **110** includes a material such as cobalt, copper or tungsten. In the illustrative embodiment, the drain contact **112** includes a barrier layer and a fill metal confined within the barrier layer. In some examples, the barrier layer includes a material such as tantalum nitride or ruthenium. In some examples, the fill metal includes a material such as cobalt, copper or tungsten.

(72) In an embodiment, the substrate **101** includes a suitable semiconductor material such as but not limited to, single crystal silicon, polycrystalline silicon and silicon on insulator (SOI) material, where a trilayer stack includes a layer of silicon oxide between two layers of monocrystalline silicon. In another embodiment, substrate **101** includes semiconductor materials such as germanium, silicon germanium or a suitable group III-N or a group III-V compound. Logic devices such as MOSFET transistors and access transistors and may also be formed on or above substrate **101**.

(73) FIG. **2A** is a cross-sectional illustration of a transistor **200** above a substrate **201**. The transistor **200** includes a channel layer **202** over a channel layer **204**, where each of the channels **202** and **204**, include a stack of two or more layers of monocrystalline transition metal dichalcogenide (TMD) materials, (herein TMD channel layer **202** and TMD channel layer **204**). In an embodiment, the TMD channel layers **202** and **204** each include a first metal. The transistor **200** further includes an encapsulation layer **206** including a second metal adjacent to the TMD channel layer **202** and TMD channel layer **204**. In exemplary embodiments, TMD channel layers **202** and **204** include a same material for optimal transistor behavior. A source contact **208** is coupled to a first end of the TMD channel layers **202** and **204** and a drain contact **210** is coupled to a second end of the TMD channel layers **202** and **204**, as shown. A gate electrode **212** is between the source contact **208** and the drain contact **210** and further between the TMD channel layer **202** and TMD channel layer **204**. A gate dielectric layer **214** is between the gate electrode **212** and the

encapsulation layer **206**.

(74) The encapsulation layer **206** is substantially the same as the encapsulation layer **104**. As discussed above in association with FIG. 1A, the encapsulation layer and TMD channels include materials that can influence the FET characteristics of a transistor. As such, the combinations of material utilized for encapsulation layer **104** and TMD channel layer **102** to obtain embodiments of N and P-type transistor **100**, may be equally applicable for encapsulation layer **206** and TMD channel layers **202** and **204** for transistor **200** described in FIG. 2A. In exemplary embodiments, the TMD channel layers **202** and **204** each include a same material. In some embodiments, TMD channel layers **202** and **204** include a metal that is different from a metal of encapsulation layer **206**.

(75) In the illustrative embodiment, the TMD channel layers **202** and **204** each have a thickness between 1 and 4 monolayers. In embodiments, each of the TMD channel layers **202** and **204** can have a same number of monolayers of TMD material or be different. In embodiments, where the TMD channel layers **202** and **204** are a single monolayer thick, the encapsulation layer **206** is on an upper and on a lower most surface of each TMD channel layers **202** and **204**. In embodiments where each of the TMD channel layers **202** and **204** have a thickness that is greater than or equal to 2 monolayers the encapsulation layer **206** is also on sidewalls of the TMD channel layer **202** and TMD channel layer **204** as shown in FIG. 2B.

(76) FIG. 2B is a cross-sectional illustration through a line A-A'. As shown, the TMD channel layer **202** has a rectangular cross-sectional profile, with a top surface **202A**, a bottom surface **202B** and sidewall surfaces **202C** and **202D**. An encapsulation layer **206** on sidewalls of TMD channel layer **202** can advantageously provide an increased surface for charge transfer. In an embodiment, the TMD channel layer **202** has a first crystallographic orientation on top surface **202A** and on bottom surface **202B**. The sidewall surfaces **202C** and **202D** may have a second crystallographic orientation. In an embodiment, the first crystallographic orientation is different from the second crystallographic orientation. The TMD channel layer **202** has a vertical thickness,  $T_{sub.V}$ , as measured from surface **202B** (along Y-direction), between 1.4 and 2.8 nm. In embodiments, the TMD channel layer **202** has a lateral thickness,  $T_{sub.L}$ , as measure from sidewall surface **202C**, (along Z-direction) between 5 nm and 60 nm.

(77) In an embodiment, the encapsulation layer **206** is at least on the top surface **202A** and on bottom surface **202B**. In the illustrative embodiment, encapsulation layer **206** is top surface **202A**, bottom surface **202B** and on sidewall surfaces **202C** and **202D**. In an embodiment, the encapsulation layer **206** is sufficiently lattice matched to the first crystallographic orientation of the TMD channel layer **202**. In an embodiment, the encapsulation layer **206** has a vertical thickness (as measured away from surfaces **202A** or **202B**) between 1 and 2 nm. In an embodiment, the encapsulation layer **206** is lattice matched to the second crystallographic orientation of the sidewall surfaces **202C** and **202D**. In an embodiment, the encapsulation layer **206** on sidewalls surfaces **202C** and **202D** has a lateral thickness (as measured away from sidewall surface **202C** and **202D**, respectively) between 1 nm and 2 nm.

(78) In embodiments, TMD channel layer **204** has one or more properties of the TMD channel layer **202** described above, such as the material composition, crystallographic orientation, and lateral and vertical thicknesses,  $T_{sub.V}$  and  $T_{sub.L}$ , respectively. As shown, the TMD channel layer **204** has a rectangular cross-sectional profile, with a top surface **204A**, a bottom surface **204B** and sidewall surfaces **204C** and **204D**.

(79) In an embodiment, the encapsulation layer **206** is on at least the top surface **204A** and on bottom surface **204B**. In the illustrative embodiment, encapsulation layer **206** is top surface **204A**, bottom surface **204B** and on sidewall surfaces **204C** and **204D**. In the illustrative embodiment, In an embodiment, the encapsulation layer **206** is lattice matched to the first crystallographic orientation of the material of TMD channel layer **204**. In an embodiment, the encapsulation layer **206** has a vertical thickness (as measured from surfaces **204A** or **204B**) between 1 and 2 nm.

(80) In an embodiment, the encapsulation layer **206** is lattice matched to the second crystallographic orientation of the sidewall surfaces **204C** and **204D**. In an embodiment, the encapsulation layer **206** on sidewall surfaces **204C** and **204D**, has a lateral thickness (as measured away from sidewall surface **204C** and **204D**, respectively) between 1 and 2 nm.

(81) As shown, the gate dielectric layer **214** clads the encapsulation layer **206**. In the illustrative embodiment, the gate electrode **212** clads the gate dielectric layer **214** and extends continuously between TMD channel layer **202** and TMD channel layer **204**.

(82) Referring again to FIG. 2A, the source contact **208** and the drain contact **210** are each spaced apart from the gate electrode **212** by a dielectric **215**. The dielectric **215** has a lateral thickness,  $S_{sub.S}$  and  $S_{sub.D}$ , respectively. In some embodiments,  $S_{sub.S}$  and  $S_{sub.D}$  are 5 nm or less.  $S_{sub.S}$  and  $S_{sub.D}$  of less than 5 nm or less may be desirable to reduce external resistance in the transistor **200**. Dielectric **215** is an insulator that can provide sufficient electrical isolation and includes silicon and one or more of oxygen, carbon or nitrogen.

(83) As shown, the encapsulation layer **206** is in contact with the source contact **208** and drain contact **210**. In some embodiments, depending on the material of the source contact **208** or the drain contact **210**, encapsulation layer **206** may advantageously reduce a Schottky barrier height between each of the TMD channel layers **202** and **204** and the respective source contact **208** and drain contact **210**. Reduction in Schottky barrier height may facilitate reduction in contact resistance.

(84) In the cross sectional illustration, the gate electrode **212** includes a gate electrode portion **212B** above the TMD channel layer **202**, a gate electrode portion **212C** between TMD channel layer **204** and template layer **218**, and a gate electrode portion **212A** between TMD channel layers **202** and **204**. The different gate electrode portions **212A**, **212B**, and **212C** are physically and electrical coupled electrically as discussed above.

(85) In an embodiment, the gate electrode **212** includes one or more layers, where a first layer in contact with the gate dielectric layer **214** is a work function electrode and a second layer in contact with the work function electrode is a fill metal. As shown, TMD channel layers **202** and **204** are spaced apart vertically by a distance  $S_{sub.V}$ .  $S_{sub.V}$  may be chosen to accommodate a combined thickness of the encapsulation layer **206**, the gate dielectric layer **214** and at least a work function portion of gate electrode **212** (in embodiments where multiple gate materials are utilized). In embodiments, gate electrode **212** includes a same material as gate electrode **108**, and gate dielectric layer **214** includes a same material as the material of the gate dielectric layer **106**, described in association with FIG. 1A.

(86) Referring again to FIG. 2A, depending on  $S_{sub.V}$ , some gate electrode portions such as gate electrode portion **212A** and **212C** may only include a work function electrode, while gate electrode portion **212B** may include a work function electrode and a fill metal. It is advantageous for the relative space,  $S_{sub.V}$ , between surface **202B** and surface **204A**, and between surfaces **204B** and **218A** (uppermost surface of template layer **218**) to have a vertical thickness that sufficiently minimizes gate capacitance. In embodiments, the height  $S_{sub.V}$ , is between 10 nm and 20 nm to provide sufficient space to form gate dielectric layer **214**, gate electrode **212**, encapsulation layer **206** and minimize gate capacitance.

(87) In an embodiment, the TMD channel layer **202** and TMD channel layer **204** each have a crystal orientation that is substantially matched to one or more underlying material. In the illustrative embodiment, TMD channel layer **202** and TMD channel layer **204** are substantially lattice matched to a plurality of templating and buffer layers where each templating and buffer layer includes a group III-Nitride (III-N) material. In an embodiment, transistor **200** includes the template layer **218** in contact with the source contact **208** and drain contact **210**, and buffer layer **220** directly below and in contact with the template layer **218**.

(88) In an embodiment, the template layer **218** includes a binary or a ternary III-N material, such as gallium nitride (GaN), one or more ternary alloys of GaN, such as AlGaN, or a quaternary alloy of

GaN including at least one group III element and nitrogen, such as In.sub.XAl.sub.YGa.sub.1-X-YN, where “X” ranges from 0.01-0.1 and “Y” ranges from 0.01-0.1. In some embodiments, the templating layer **218** includes AlInN. The template layer **218** provides a template for hexagonal crystal in TMD channel layer **202** and TMD channel layer **204**. The template layer **218** is an electrically non-conductive layer. In the illustrative embodiment, the encapsulation layer **206** is in direct contact with an uppermost surface **218A** of the template layer.

(89) In an embodiment, the buffer layer **220** includes a single layer of AlN. In embodiments, the thickness of the AlN buffer layer **220** is between 100 nm and 400 nm. In an embodiment, the substrate **201** includes a single crystal silicon, or a silicon on insulator (SIO) substrate.

(90) For a given TMD material, the material of the encapsulation layer **206** may be chosen to form an N-type FET or a P-type FET. As such, two stacked nanosheet TMD transistors such as transistor **200** with a same TMD material but different encapsulation material may be adjacent to each other on a same plane of a shared substrate to obtain a complimentary N-FET and P-FET.

(91) FIG. 2C is a cross-sectional illustration of a transistor array **250** including transistor **200A** adjacent to transistor **200B**, above a shared substrate **201**. As shown, transistor **200A** is electrically isolated from transistor **200B** by dielectric **215**.

(92) In the illustrative embodiment, transistor **200A** is the same as transistor **200**. In an embodiment, transistor **200A** is an N-type FET and transistor **200B** is a p-type FET. In other embodiments, transistor **200A** is a P-type FET and the transistor **200A** is an N-type FET. As shown transistor **200B** includes TMD channel layers **202** and **204**, gate dielectric layer **214** adjacent to each of the TMD channel layers **202** and **204**, and a gate electrode **212** adjacent to the gate dielectric layer **214**. The transistor **200B** further includes a source contact **208** in contact with TMD **202** and **204**, and a drain contact **210** in contact with TMD channel layers **202** and **204**.

(93) In an exemplary embodiment, transistor **200B** has substantially the same features as transistor **200A**, except that the transistor **200B** includes no encapsulation layer **206**. In one such exemplary embodiment, transistor **200A** includes an Al.sub.2O.sub.3-encapsulation layer **206** and a WSe.sub.2 TMD channel layers **202** and **204**. In one such embodiment, transistor **200A** exhibits N-FET behavior. In some such embodiment, transistor **200B** with WSe.sub.2 TMD channel layers **202** and **204** exhibits a P-FET behavior because of an absence of the Al.sub.2O.sub.3-encapsulation layer **206**.

(94) In embodiments source contact **208** and drain contact **210** each include a material of the source contact **110** or drain contact **112** described in association with FIG. 1A.

(95) In some embodiments, an N and a P type transistor may both include an encapsulation layer. FIG. 2D is a cross-sectional illustration of a transistor array **260** including transistor **200A** adjacent to transistor **200C**, above a shared substrate **201**. In the illustrative embodiment, transistor **200A** is the same as transistor **200**. In an embodiment, transistor **200A** is an N-type FET and transistor **200B** is a p-type FET. In other embodiments, transistor **200A** is a P-type FET and the transistor **200A** is an N-type FET. As shown transistor **200B** includes TMD channel layers **202** and **204**, an encapsulation layer **216** adjacent to each of the TMD channel layers **202** and **204**, and a gate dielectric layer **224** adjacent to the encapsulation layer **216** and between the encapsulation layer **216** and gate electrode **222**. In exemplary embodiments, encapsulation layers **206** and **216**, each include a different metal.

(96) In further specific examples, the TMD channel layers **202** and **204** each include sulfides of molybdenum, tungsten, titanium or chromium. In some such embodiments, the encapsulation layer **206** includes oxygen and aluminum, or sub-stoichiometric aluminum oxide, and the encapsulation layer **216** includes oxygen and molybdenum or tungsten, or sub-stoichiometric tungsten oxide or molybdenum oxide, or vice versa. In some exemplary embodiments, TMD channel layers **202** and **204** each include WS.sub.2 and encapsulation layer **206** includes aluminum oxide and the encapsulation layer **216** includes tungsten oxide.

(97) In embodiments, gate electrode **222** includes a material that is the same or substantially the

same as the material of the gate electrode **212**. In other embodiments, gate electrode **222** of transistor **200C** includes a different material than a material of the gate electrode **212** of transistor **200A**. Different gate electrode materials may be implemented to advantageously tune threshold voltage for respective N and P transistors. In embodiments gate dielectric layer **224** includes a material that is the same or substantially the same as the material of the gate dielectric layer **106** described in association with FIG. **1A**.

(98) Referring again to FIG. **2D**, in embodiments, gate dielectric layer **224** includes a material that is the same or different from a material of the gate dielectric layer **216**. Examples of gate dielectric materials include hafnium oxide, hafnium silicon oxide, lanthanum oxide, lanthanum aluminum oxide, zirconium oxide, zirconium silicon oxide, tantalum oxide, titanium oxide, barium strontium titanium oxide, barium titanium oxide, strontium titanium oxide, yttrium oxide, lead scandium tantalum oxide or lead zinc niobate. In embodiments the gate dielectric layers **214** and **224** each have a thickness between 0.8 nm and 4 nm. The gate dielectric layers **214** and **224** may have a same or different thicknesses.

(99) The transistor further includes a source contact **218** in contact with TMD **202** and **204**, and a drain contact **220** in contact with TMD **202** and **204**. In embodiments, source contact **218** and drain contact **220** each include a material that is the same or substantially the same as the material of the source contact **208** and drain contact **210**.

(100) FIG. **3** is a method **300** to fabricate a transistor depicted in FIG. **2A**, in accordance with an embodiment of the present disclosure. The method **300** begins at operation **310** by patterning a material layer stack comprising a layer of a III-N material on a plurality of bilayers into a block having sidewalls. The method **300** continues at operation **320** by forming a dielectric adjacent to the block. The method **300** continues at operation **330** with a process of etching and remove a portion of the dielectric to form an exposed portion of the block and etching and removing the layer of III-N material to suspend a plurality of channel layers in the exposed portion of the block. The method **300** continues at operation **340** with formation of a liner to clad the plurality of channel layers in the exposed portion of the block. The method **300** continues at operation **350** with the formation of a gate between each of plurality of channel layers in a first portion of the exposed portion of the block. The method **300** concludes at operation **360** with the formation of a first contact in a second portion of the block and a second contact in a third portion of the block, wherein the first portion is between the second portion and the third portion.

(101) FIG. **4A** is a cross-sectional illustration of material layer stack **400** for fabrication of a TMD transistor device, in accordance with an embodiment of the present disclosure. As shown, a buffer layer **220** is formed on the substrate **201**.

(102) In an embodiment, the buffer layer **220** is formed to overcome lattice and thermal mismatch between the substrate **201** and a group III-N semiconductor material to be formed above. The buffer layer **220** may be grown on the substrate **201** by a metal organic chemical vapor deposition (MOCVD) process at a temperature in the range of 1000-1100 degrees Celsius. Depending on embodiments, the buffer layer **220** includes nitrogen and one or more of, Al, In or Ga, for example Al.sub.zGa.sub.1-zN, Al.sub.wIn.sub.1-wN, or AlN. In exemplary embodiments buffer layer **220** includes AlN. In an embodiment, an AlN buffer layer **220** has a hexagonal wurtzite structure. The buffer layer **220** including AlN may be grown to a thickness between 25 nm and 100 nm. In other embodiments, the buffer layer **220** includes a plurality of layers of III-N materials above the substrate **201**. The layers may be interleaved with two or more layers of III-N materials such as but not limited to Al.sub.zGa.sub.1-zN, Al.sub.wIn.sub.1-wN, or AlN.

(103) The template layer **218** is formed on the buffer layer **220**. In an embodiment, the template layer **218** is formed by an MOVCD epitaxy process. The template layer **218** is deposited to a thickness between 10 nm and 50 nm. In an embodiment, the template layer **218** is a layer of GaN. In an embodiment, the GaN template layer **218** is grown to a thickness that is between 100 nm and 400 nm. A GaN template layer **218** may have a defect density less than (1e10/cm<sup>2</sup>) when grown to

a thickness of at least 100 nm.

(104) The process continues with formation of a material layer stack **400** having a plurality of bilayers **401** on the template layer **218**. In the illustrative embodiment, two bilayers **401** are shown. In the illustrative embodiment, each bilayer includes a layer **402** and a layer **403** on layer **402**, where layer **403** includes a TMD material. As shown, material layer stack **400** further includes another layer of layer **402** on layer **403**.

(105) In an embodiment, the layer **402** includes a group III-N material. In an exemplary embodiment, layer **402** includes nitrogen and one or more of Al or In. In an exemplary embodiment, layer **402** includes AlN. An AlN layer **402** can be grown by MOCVD epitaxially on the template layer **218** and provides a surface for graphoepitaxy growth of the TMD layer **403**. In embodiments, the TMD layers **403** have a substantially the same crystal structure as an AlN layer **402**. In embodiments where the AlN layer **402** is single crystalline, templating a TMD layer **403** off the AlN layer **402**, facilitates optimizing grain size of the TMD layer **403**. The layer **402** also provides sufficiently high etch selectivity (greater than 5:1) relative to the template layer **218**. In embodiments, AlN layer **402** is grown to a thickness of at least 6 nm.

(106) The TMD layer **403** is formed on layer **402**, where TMD layer **403** includes a material of the TMD channel layer **202** or TMD channel layer **204** (described in association with FIG. 2A). Depending on embodiments, TMD layer **403** has a thickness that is between 1 to 4 monolayers. The TMD layer **403** is formed by an MOCVD or a CVD process. The TMD layer **403** is formed on a top surface of layer **402** as shown. In an embodiment, the TMD layer is synthesized by a chemical vapor deposition process (CVD) or a molecular beam epitaxy process (MOCVD) process. Depending on processing embodiments, chemical synthesis uses a solid or a gaseous precursor. In one embodiment, a CVD process utilizes a solid precursor such as a transition metal oxide and a pure chalcogen to coat exposed surface of layer **402**. A CVD furnace may be utilized to form the TMD layer **403**, where the TMD layer **403** may be deposited at a process temperature of at least 600 degrees Celsius. In MOCVD embodiments, chemical synthesis utilizes a gaseous precursor and the TMD layer **403** is deposited at a process temperature of at least 300 degrees Celsius. In an embodiment, the process utilized to form the TMD layer forms a single monolayer of TMD layer **403**. The material layer stack **400** includes a same TMD material within each bilayer **401** and is formed to a substantially same thickness. In some embodiments, a layer **403** including 2 to 4 monolayers of TMD is formed on each layer **402**. In other embodiments, layer **403** has different thicknesses from one bilayer **401** to the next. In an embodiment, the process to form the bilayer **401** is repeated until a desired number of TMD channel layers is formed. While two bilayers **401** are shown, the number of bilayers can be between 2-10.

(107) FIG. 4B is a cross sectional illustration of a block **406** formed by patterning the material layer stack **400** depicted in FIG. 4A. In an embodiment, a plasma etch process may be utilized to pattern the material layer stack **400** into a block **406**. In exemplary embodiments, the sidewalls **406A** and **406B** of the block **406** are substantially vertical with respect to an uppermost surface **218A**, as shown. The patterning process carried out to etch the block **406**, etches the lowermost layer **402** directly above template layer **218**. The etch process is halted after exposure of the template layer **218**.

(108) FIG. 5A illustrates the structure of FIG. 4B following the formation of a dielectric **408** on the block and following the formation of a mask **412**. In an embodiment, the dielectric **408** includes a material that can provide electrical isolation. Examples of dielectric **408** include silicon and one or more of nitrogen, oxygen or carbon.

(109) In the illustrative embodiment, a dielectric **408** is deposited on and surrounds the block **406**. After deposition, the dielectric **408** may be planarized. In an embodiment, dielectric **408** is planarized using a chemical mechanical polish (CMP) process. As shown, the dielectric **408** may be planarized until an uppermost surface **408A** of the dielectric **408** is coplanar or substantially coplanar with an uppermost surface **406A** of the block **406**. A mask **412** is formed on top of the

dielectric **408** and on a portion of the block **406**. A plan view depicting a shape of the mask **412** and exposed block **406** is illustrated in FIG. **4B**. Pair of dashed lines **407** indicate portions of the block **406** that are covered by the mask **412**.

(110) FIG. **6A** is a cross-sectional illustration of a plurality of nanosheets formed above a substrate **201**. In the illustrative embodiment, the dielectric **408** is patterned and the mask **412** is removed. The patterning process creates an opening **413**.

(111) The layer **402** from each bilayer is selectively removed. In an embodiment, a wet chemical etch, a vapor etch process, or a combination thereof is utilized to selectively remove the layer **402**. The process of removing the layer **402** from each bilayer forms TMD channel layers **410** and **412** as shown. The TMD channel layers **410** and **412** remain anchored to the dielectric **408** after the selective etch process. Portions of the layer **402** that were covered by the mask during the dielectric etch process may remain adjacent to the dielectric **408**, such as is illustrated. In other embodiments, layer **402** is completely removed. In embodiments, TMD channel layers **410** and **412** include one or more properties of the TMD channel layers **202** and **204**, such as material and thickness, described in association with FIGS. **2A** and **2B**.

(112) FIG. **6B** is a plan-view illustration of the structure in FIG. **6A**. As shown template layer **218** is exposed by the etch process. The etch process also exposes sidewalls **406A** and **406B** of the block **406**, as is shown in FIG. **6B**. Exposing the sidewalls **406A** and **406B** are important for the process of releasing the layer **402**. In the illustrative embodiment, the etch process removes portions of the layer **402** from the sidewalls **406A** and **406B** and etches inward as indicated by arrows **415** along the  $\pm z$ -direction, in the Figure.

(113) FIG. **7A** is a cross-sectional illustration of the structure in FIG. **6A** following the process to form an encapsulation layer **418** on each of the TMD channel layers **410** and **412**. In an embodiment, an encapsulation layer **418** is formed by a CVD or an atomic layer deposition (ALD) process. In some embodiments, the encapsulation layer **418** is formed selectively on uppermost surface **410A** and on lowermost surface **410B** of the TMD channel layer **410**. As shown, encapsulation layer **418** is also formed selectively on uppermost surface **412A** and lowermost surface **412B** of TMD channel layer **412**. In the illustrative embodiment, the encapsulation layer **418** is also formed on uppermost surface **218A** of template layer **218**. In some embodiments, the encapsulation layer **418** is also formed on sidewalls **408B** and **408C** and on uppermost surface **408A** of the dielectric **408** (as indicated by dashed lines **420**). The encapsulation layer **418** may be lattice matched with the TMD material to obtain band alignment between TMD material and the material of the encapsulation layer **418**. Band alignment may promote transfer of charge between the encapsulation layer **418** and TMD material. In some embodiments, the encapsulation layer **418** is deposited to a thickness of 1 nm and 3 nm.

(114) The encapsulation layer **418** may be chosen to form an N-type FET or a P-type FET. In an embodiment, the encapsulation layer **418** includes oxygen and one of aluminum, molybdenum or tungsten, for e.g., aluminum oxide, tungsten oxide, or molybdenum oxide. In other embodiments, the encapsulation layer **418** includes a sub-stoichiometric aluminum oxide, tungsten oxide, or molybdenum oxide. The encapsulation layer **418** is designed to attract electrons from or donate electrons to the TMD channel layers **410** and **412**. Attracting electrons from the encapsulation layer **418** may introduce shallow acceptor states close to the valence band edge of the TMD channel layers **410** and **412** creating a P-type doping effect. Donating electrons to TMD channel layers **410** and **412** from encapsulation layer **418** may introduce shallow donor states close to a conduction band edge, leading to N-type doping effect. In embodiments, control of the electron donor and acceptor level may be controlled by changing the level of defects in the encapsulation layer **418**. In some embodiments, the encapsulation layer **418** is deposited with a defect level of greater than  $1e13/cm^2$ .

(115) The TMD channel layers **410** and **412** may be intrinsically N-type or P-type semiconducting TMDs. N-type TMD channel layers **410** and **412** include for e.g., sulfides of Mo, W, Ti. In some



such embodiments, deposition of an encapsulation layer **418** including tungsten oxide may enable P-type doping effect in an N type TMD nanosheet transistor.

(116) In some exemplary embodiments, TMD channel layers **410** and **412** includes WSe.sub.2. A transistor fashioned from a WSe.sub.2 TMD channel layers **410** and **412** may exhibit P-type behavior. In some such embodiments, an encapsulation layer **418** including Al and O, e.g., Al.sub.2O.sub.3, can result in P-type WSe.sub.2 TMD channel layers **410** and **412** to exhibit N-type behavior in a TMD transistor during voltage biasing.

(117) FIG. 7B is a cross-sectional illustration along a line A-A' through the structure in FIG. 7A. In embodiments, where the TMD channel layers **410** and **412** each include more than one monolayer, the cross sectional profile of the TMD channel layers **410** and **412** can be rectangular as illustrated (and described in association with FIG. 2B). In some embodiments, an atomic layer deposition (ALD) process to entirely clad the TMD channel layers **410** and **412** with the encapsulation layer **418**, as shown.

(118) It is to be appreciated that in embodiments, an N and a P type TMD nanosheet transistor may be co-fabricated. In one example, TMD layers in multiple transistor structures may be released. An encapsulation layer may be formed on a selected transistor structure after masking a different transistor structure. In a second embodiment, TMD layers are released in a first transistor structure, while a second transistor structure is masked.

(119) FIG. 8 is a structure **800** that includes a device structure **800A** adjacent to a device structure **800B**. Device structures **800A** and **800B** will be formed into transistors. The device structure **800A** is substantially the same as the device structure in FIG. 5A, except where the mask **412** is replaced by a mask **421** in FIG. 8. As shown, mask **421** extends over the entire device structure **800B**.

(120) In one or more embodiments, the device structure **800** is formed as described above. After formation of the encapsulation layer **418** on TMD channel layers **410** and **412**, the fabrication process may be continued on device structure **800A** while the device structure **800B** is masked.

(121) FIG. 9A is a cross-sectional illustration of the structure **800A** in FIG. 8A following the formation of a dummy gate structure **422** in the opening and following the deposition of dielectric **424** after formation of the dummy gate structure **422**.

(122) The material of the dummy gate structure is chosen to facilitate patterning as well as selective removal with respect to the dielectric **424** and encapsulation layer **418**. In an embodiment, a polycrystalline silicon material is deposited into the opening **425**. A polycrystalline silicon material advantageously offers ease of patterning and selective removal with respect to the encapsulation layer **418**. After deposition the polycrystalline silicon material is planarized and patterned into a dummy gate structure **422**. The dummy gate structure also includes portions **422A** and **422B** between the TMD channel layers **410** and **412** and between TMD layers **412** and template layer **418**, respectively and a portion **422C** above the TMD channel layer **410**. Portions **422A**, **422B** and **422C** will be replaced by a gate structure including a gate dielectric layer and a gate electrode in a subsequent operation.

(123) After the formation of the dummy gate structure **422** a dielectric **424** is blanket deposited into the opening **425** and planarized. In some embodiments, the dielectric **424** includes silicon and one or more of nitrogen, oxygen or carbon. The material of the dielectric **424** may affect the capacitance in a TMD nanosheet transistor to be formed. In one embodiment, the dielectric **424** is a silicon nitride. In other embodiments, the dielectric **424** includes a material having a low dielectric constant, such as a dielectric constant equal to or below 2. In embodiments, dielectric **424** is silicon oxide or silicon carbide.

(124) FIG. 9B illustrates the structure of FIG. 9A following the removal of the dummy gate structure **422** (not shown in Figure). In an embodiment, a plasma etch process may be performed to remove a first portion of the dummy gate structure **422**, followed by a wet chemical process to remove a remaining second portion. The dummy gate structure **422** is removed from between the TMD channel layers **410** and **412**, from between TMD layers **412** and template layer **418**, and from

above the TMD channel layer **410**. The process of removing the dummy gate structure **422** does not etch the encapsulation layer **418**.

(125) FIG. **10A** illustrates the structure of FIG. **9B** following the formation of a gate structure **428** in the opening **426** formed after removal of the dummy gate structure. In an embodiment, the process begins by forming a gate dielectric layer **430** in the opening **426** on all exposed surfaces of the encapsulation layer **418**. In an embodiment, the gate dielectric layer **430** is deposited by an atomic layer deposition (ALD) process. The ALD process forms a conformal layer of gate dielectric layer **430** on surfaces of the encapsulation layer **418**, and on the template layer **218**, on uppermost surfaces of dielectrics **408** and **424**. In an embodiment, the gate dielectric layer **430** is deposited to a thickness between 0.8 nm and 4 nm. A material of a gate electrode **432** is deposited on the gate dielectric layer **430** in the opening **426** and above the dielectrics **408** and **424**. In an embodiment, an ALD process is utilized to deposit the gate electrode material between the TMD layers **410** and TMD channel layer **412**, between TMD channel layer **412** and template layer **418** and above TMD channel layer **410**.

(126) In an embodiment, after the deposition process the gate electrode material and the gate dielectric layer **430**, from above the dielectric **408** and dielectric **424**, are removed by a CMP process to form gate structure **428**.

(127) FIG. **10B** is a cross sectional illustration through a line A-A' in FIG. **10A**. In an embodiment, the gate electrode **432** is a single connected continuous portion, extending between each respective TMD channel layers **410** and **412**, as shown. In the illustrative embodiment, the gate dielectric layer **430** clads the encapsulation layer **418** formed around each of the TMD channel layers **410** and **412**.

(128) FIG. **11A** is a cross-sectional illustration of the structure in FIG. **10A** following the formation of openings **433A** and **433B** to deposit source and drain contact material. In an embodiment, a plasma etch process is utilized to form openings **433A** and **433B** after the formation of a mask on dielectric **408** and **424**, on the gate dielectric layer **430** and on the gate electrode **432**. In an embodiment, the dielectric **408** and the dielectric **424** are etched by a plasma etch process to form openings **433A** and **433B**.

(129) In an embodiment, opening **433A** exposes the encapsulation layer **418** adjacent to a first portion TMD channel layers **410** and **412** and an opening **433B** exposes the encapsulation layer **418** adjacent to second portion of the TMD channel layers **410** and **412**, as shown. In an embodiment, the openings **433A** and **433B** can extend to gate dielectric layer **430**. In the illustrative embodiment, a portion of dielectric **424** is adjacent to gate dielectric layer **430** to provide electrical isolation when the gate dielectric layer has a thickness that is comparable to 1 nm. In the illustrative embodiment, the plasma etch process utilized to form openings **433A** and **433B** has sufficient isotropic etch components to advantageously remove the dielectric layer **424** from regions between TMD channel layers **410** and **412**, and between TMD layers **412** and template layer **218**. Removal of the dielectric **408** and **422** between TMD channel layers **410** and **412**, and between TMD layers **412** and template layer **218** enables contacts to be formed adjacent to encapsulation layer **418**. In exemplary embodiments, template layer **218** does not need to be exposed as long as dielectric **424** adjacent the encapsulation layer portion **418A** is removed.

(130) In an embodiment, the etch process can remove portions of the encapsulation layer **418** from above the TMD channel layer **410** as shown in FIG. **11B**. Referring again to FIG. **11A**, in some embodiments, the etch process is also sufficiently isotropic that portions of the encapsulation layer **418** between the TMD channel layer **410** and **412** within the openings **433A** and **433B** are also removed during formation of opening **433A** and **433B**. It is to be appreciated that the portion of the encapsulation layer **418** masked by the dielectric **424** is not removed even if exposed portions of the encapsulation layer **418** may be etched. Encapsulation layer **418** adjacent to gate dielectric layer **430** but directly under (or above) dielectric **424** may advantageously provide charge transfer between source contact and channel portions of the TMD channel layers **410** and **412** (region under

and between portions of gate electrode **432**). Encapsulation layer **418** adjacent to gate dielectric layer **430** but directly under dielectric **424** may help reduce access resistance between gate and drain or between gate and source.

(131) It is to be appreciated that the etch process is selective to the gate dielectric layer **430**. In embodiments, a gate dielectric layer **430** including a high-dielectric constant material such as  $\text{HfO}_2$  or  $\text{ZrO}_2$  etc, can provide sufficient etch selectivity against removal of the encapsulation layer **418**.

(132) FIG. **12** illustrates the structure of FIG. **11A** following the formation of source contact **434** and drain contact **436** in the openings **433A** and **433B**, respectively. In an embodiment, one or more layers of contact material are blanket deposited on exposed surfaces of the encapsulation layer **418** and on uppermost surface of the dielectrics **408** and **424**, gate dielectric layer **430**, gate electrode **432**, and template layer **218**. In an embodiment, the contact material includes one or more layers of conductive materials that are substantially the same as the material of the source contact **110** and drain contact **112** (described in association with Figure. In an embodiment, the one or more layers of conductive material are deposited in the openings **433A** and **433B**. In an embodiment, a planarization process is utilized to remove the excess one or more layers of conductive material formed on uppermost surface of the dielectric **424**, dielectric **408**, gate dielectric layer **430** and gate electrode **432**. The planarization process forms source contact **434** and drain contact **436** of transistor **1200**.

(133) FIG. **13** is a structure **800**, including a transistor **1200** adjacent to the device structure **800B** (from FIG. **8**). In an embodiment, a mask can be formed above transistor **1200** and the device structure **800** can evolve through a sequence of operations similar to operations outlined herein to fabricate a second transistor directly adjacent to transistor **1200**. The second transistor may or may not be fabricated with an encapsulation layer.

(134) FIG. **14A** illustrates a cross-sectional view of a memory cell **1400** including a nanosheet transistor with a plurality of TMD channels, such as transistor **1200** and a non-volatile memory element **1402** coupled to a drain contact **436** of the transistor **1200**. In the illustrative embodiment, the non-volatile memory element **1402** is coupled to the drain contact **436** of the transistor **1200**.

(135) Non-volatile memory element **1402** may include a magnetic tunnel junction (MTJ) device, a conductive bridge random access memory (CBRAM) device, or a resistive random-access memory (RRAM) device. A non-volatile memory element such as an MTJ device requires a nominal critical switching current, that depends on an MTJ device area, to undergo magnetization switching. As an MTJ is scaled down in size, the critical switching current required to switch the memory state of the MTJ device also scales proportionally with device area, however scaling MTJ's presents numerous challenges. If a transistor connected to an MTJ device can deliver an amount of current that exceeds critical switching current requirement of the MTJ device, then feature size scaling of MTJ devices can be relaxed. In an embodiment, transistor **1200**, which can provide an additional current boost (through increase in drive current), can be advantageously coupled to non-volatile memory element **1402** such as an MTJ device to overcome any larger critical switching current requirements.

(136) FIG. **14B** illustrates a cross-sectional view of an example non-volatile memory element **1402** that includes a magnetic tunnel junction (MTJ) material device. In the illustrated embodiment, the MTJ device includes a bottom electrode **1404**, a fixed magnet **1406** above the bottom electrode **1404**, a tunnel barrier **1408** on the fixed magnet **1406**, a free magnet **1410** on the tunnel barrier **1408**, and a top electrode **1412** on the free magnet **1410**. In an embodiment, a dielectric spacer laterally surrounds (not shown) non-volatile memory element **1402**.

(137) In an embodiment, fixed magnet **1406** includes a material and has a thickness sufficient for maintaining a fixed magnetization. For example, fixed magnet **1406** may include an alloy such as  $\text{CoFe}$  and  $\text{CoFeB}$ . In an embodiment, fixed magnet **1406** includes  $\text{Co}_{X-100}\text{Fe}_Y\text{B}_Z$ , where X and Y each represent atomic percent such that X is between 50 and 80 and Y is between

10 and 40, and the sum of X and Y is less than 100. In an embodiment, X is 60 and Y is 20. In an embodiment, fixed magnet **1406** is FeB, where the concentration of boron is between 10 and 40 atomic percent of the total composition of the FeB alloy. In an embodiment, the fixed magnet **1406** has a thickness that is between 1 nm and 2.5 nm.

(138) In an embodiment, tunnel barrier **1408** is composed of a material suitable for allowing electron current having a majority spin to pass through tunnel barrier **1408**, while impeding, at least to some extent, electron current having a minority spin from passing through tunnel barrier **1408**. Thus, tunnel barrier **1408** (or spin filter layer) may also be referred to as a tunneling layer for electron current of a particular spin orientation. In an embodiment, tunnel barrier **1408** includes a material such as, but not limited to, magnesium oxide (MgO) or aluminum oxide (Al.sub.2O.sub.3). In an embodiment, tunnel barrier **1408** including MgO has a crystal orientation that is (001) and is lattice matched to free magnet **1410** above tunnel barrier **1408** and fixed magnet **1406** below tunnel barrier **1408**. In an embodiment, tunnel barrier **1408** is MgO and has a thickness is between 1 nm to 2 nm.

(139) In an embodiment, free magnet **1410** includes a magnetic material such as Co, Ni, Fe or alloys of these materials. In an embodiment, free magnet **1410** includes a magnetic material such as FeB, CoFe and CoFeB. In an embodiment, free magnet **1410** includes a Co.sub.100-x-yFe.sub.xB.sub.y, where X and Y each represent atomic percent such that X is between 50 and 80 and Y is between 10 and 40, and the sum of X and Y is less than 100. In an embodiment, X is 60 and Y is 20. In an embodiment, free magnet **1410** is FeB, where the concentration of boron is between 10 and 40 atomic percent of the total composition of the FeB alloy. In an embodiment, free magnet **1410** has a thickness that is between 1 nm and 2.0 nm.

(140) In an embodiment, bottom electrode **1404** includes an amorphous conductive material. In an embodiment, bottom electrode **1404** is a topographically smooth electrode. In an embodiment, bottom electrode **1404** includes a material such as W, Ta, TaN or TiN. In an embodiment, bottom electrode **1404** is composed of Ru layers interleaved with Ta layers. In an embodiment, bottom electrode **1404** has a thickness between 20 nm and 50 nm. In an embodiment, top electrode **1412** includes a material such as W, Ta, TaN or TiN. In an embodiment, top electrode **1412** has a thickness between 30 nm and 70 nm. In an embodiment, bottom electrode **1404** and top electrode **1412** are the same metal such as Ta or TiN. In an embodiment, the MTJ device has a combined total thickness of the individual layers is between 60 nm and 100 nm and a width is between 10 nm and 50 nm.

(141) Referring again to FIG. **14A**, in an embodiment, non-volatile memory element **1402** is a resistive random-access memory (RRAM) that operates on the principle of filamentary conduction. When an RRAM device undergoes an initial voltage breakdown, a filament is formed in a layer known as a switching layer. The size of the filament depends on the magnitude of the breakdown voltage and reliable switching between different resistance states in a filamentary RRAM device can be greatly enhanced at larger current. In an embodiment, transistor **1200**, that can provide an additional current boost (through increase in drive current), can be advantageously coupled to an RRAM device to provide reliable switching operation.

(142) FIG. **14C** illustrates a cross-sectional view of an example non-volatile memory element **1402** that includes a resistive random-access memory (RRAM) device. In the illustrated embodiment, the RRAM material stack includes a bottom electrode **1414**, a switching layer **1416** over the bottom electrode **1414**, an oxygen exchange layer **1418** over the switching layer **1416**, and a top electrode **1420** on the oxygen exchange layer **1418**.

(143) In an embodiment, bottom electrode **1414** includes an amorphous conductive layer. In an embodiment, bottom electrode **1414** is a topographically smooth electrode. In an embodiment, bottom electrode **1414** includes a material such as W, Ta, TaN or TiN. In an embodiment, bottom electrode **1414** is composed of Ru layers interleaved with Ta layers. In an embodiment, bottom electrode **1414** has a thickness is between 20 nm and 50 nm. In an embodiment, top electrode **1420**

includes a material such as W, Ta, TaN or TiN. In an embodiment, top electrode **1420** has a thickness is between 140 and 70 nm. In an embodiment, bottom electrode **1414** and top electrode **1420** are the same metal such as Ta or TiN.

(144) Switching layer **1416** may be a metal oxide, for example, including oxygen and atoms of one or more metals, such as, but not limited to Hf, Zr, Ti, Ta or W. In the case of titanium or hafnium, or tantalum with an oxidation state +4, switching layer **1416** has a chemical composition,  $\text{MO.sub.X}$ , where O is oxygen and X is or is substantially close to 2. In the case of tantalum with an oxidation state +5, switching layer **1416** has a chemical composition,  $\text{M.sub.2Ox}$ , where O is oxygen and X is or is substantially close to 5. In an embodiment, switching layer **1416** has a thickness is between 1 nm and 5 nm.

(145) Oxygen exchange layer **1418** acts as a source of oxygen vacancy or as a sink for  $\text{O.sup.2-}$ . In an embodiment, oxygen exchange layer **1418** is composed of a metal such as but not limited to, hafnium, tantalum or titanium. In an embodiment, oxygen exchange layer **1418** has a thickness is between 5 nm and 20 nm. In an embodiment, the thickness of oxygen exchange layer **1418** is at least twice the thickness of switching layer **1416**. In another embodiment, the thickness of oxygen exchange layer **1418** is at least twice the thickness of switching layer **1416**. In an embodiment, the RRAM device has a combined total thickness of the individual layers is between 60 nm and 100 nm and width is between 10 nm and 50 nm.

(146) Referring again to FIG. **14A**, the memory device **1402** is coupled to the transistor **1200** through interconnect structures at a level **1422** above the transistor. In an embodiment, level **1422** includes a single level of interconnects coupled with the transistor **1200**. In other embodiments, level **1422** includes a plurality of sublevels of interconnect routing structures.

(147) In the illustrative embodiment, the memory cell **1400** includes a drain interconnect **1424** between the memory device **1402** and the drain contact **436**. As shown, the drain interconnect **1424** is on and coupled with the drain contact **436**. The memory cell **1400** further includes a source interconnect **1426** coupled with the source contact **434** and gate interconnect **1428** coupled with the gate **432**. In other embodiments, a gate contact is between the gate **432** and the gate interconnect **1428**. The memory device **1402** is further coupled to a memory interconnect **1430**.

(148) In an embodiment, source interconnect **1426**, gate interconnect **1428** and drain interconnect **1424** are embedded in a dielectric layer **1432**. In an embodiment, the source interconnect **1426**, gate interconnect **1428**, drain interconnect **1424** and memory interconnect **1430** each include titanium, tantalum, tungsten, ruthenium, copper, or nitrides of titanium, tantalum, tungsten, ruthenium. In other embodiments the source interconnect **1426**, gate interconnect **1428**, drain interconnect **1424** and memory interconnect **1430**, include a liner layer including ruthenium or tantalum and a fill metal such as copper or tungsten. In the illustrative embodiment, the memory device **1402** and the memory interconnect **1430** is embedded in a dielectric **1434**.

(149) In an embodiment, the level **1422** further includes a barrier dielectric layer **1436** between the dielectric **1432** and dielectric **1434**. In embodiments dielectric **1432** and **1434** include silicon and one or more of nitrogen, oxygen and carbon such as, silicon nitride, silicon dioxide, carbon doped silicon nitride, silicon oxynitride or silicon carbide.

(150) In embodiments, dielectric **1436** includes silicon and one or more of nitrogen and carbon such as, silicon nitride, carbon doped silicon nitride or silicon carbide.

(151) FIG. **15** illustrates a computing device **1500** in accordance with embodiments of the present disclosure. As shown, computing device **1500** houses a motherboard **1502**. Motherboard **1502** may include a number of components, including but not limited to a processor **1501** and at least one communications chip **1504** or **1505**. Processor **1501** is physically and electrically coupled to the motherboard **1502**. In some implementations, communications chip **1505** is also physically and electrically coupled to motherboard **1502**. In further implementations, communications chip **1505** is part of processor **1501**.

(152) Depending on its applications, computing device **1500** may include other components that

may or may not be physically and electrically coupled to motherboard **1502**. These other components include, but are not limited to, volatile memory (e.g., DRAM), non-volatile memory (e.g., ROM), flash memory, a graphics processor, a digital signal processor, a crypto processor, a chipset **1506**, an antenna, a display, a touchscreen display, a touchscreen controller, a battery, an audio codec, a video codec, a power amplifier, a global positioning system (GPS) device, a compass, an accelerometer, a gyroscope, a speaker, a camera, and a mass storage device (such as hard disk drive, compact disk (CD), digital versatile disk (DVD), and so forth).

(153) Communications chip **1505** enables wireless communications for the transfer of data to and from computing device **1500**. The term “wireless” and its derivatives may be used to describe circuits, devices, systems, methods, techniques, communications channels, etc., that may communicate data through the use of modulated electromagnetic radiation through a non-solid medium. The term does not imply that the associated devices do not contain any wires, although in some embodiments they might not. Communications chip **1505** may implement any of a number of wireless standards or protocols, including but not limited to Wi-Fi (IEEE 801.11 family), WiMAX (IEEE 801.11 family), long term evolution (LTE), Ev-DO, HSPA+, HSDPA+, HSUPA+, EDGE, GSM, GPRS, CDMA, TDMA, DECT, Bluetooth, derivatives thereof, as well as any other wireless protocols that are designated as 3G, 4G, 5G, and beyond. Computing device **1500** may include a plurality of communications chips **1504** and **1505**. For instance, a first communications chip **1505** may be dedicated to shorter range wireless communications such as Wi-Fi and Bluetooth and a second communications chip **1504** may be dedicated to longer range wireless communications such as GPS, EDGE, GPRS, CDMA, WiMAX, LTE, Ev-DO, and others.

(154) Processor **1501** of the computing device **1500** includes an integrated circuit die packaged within processor **1501**. In some embodiments, the integrated circuit die of processor **1501** includes one or more interconnect structures, non-volatile memory devices, and transistors such as TMD nanosheet transistors **100**, **200**, or transistor arrays **250** or **260** respectively. The term “processor” may refer to any device or portion of a device that processes electronic data from registers and/or memory to transform that electronic data into other electronic data that may be stored in registers and/or memory.

(155) Communications chip **1505** also includes an integrated circuit die packaged within communication chip **1505**. In another embodiment, the integrated circuit die of communications chips **1504**, **1505** includes one or more interconnect structures, non-volatile memory devices, capacitors and transistors such as TMD nanosheet transistors **100**, **200**, or transistor arrays **250** or **260**, described above. Depending on its applications, computing device **1500** may include other components that may or may not be physically and electrically coupled to motherboard **1502**. These other components may include, but are not limited to, volatile memory (e.g., DRAM) **1507**, **1508**, non-volatile memory (e.g., ROM) **1510**, a graphics CPU **1512**, flash memory, global positioning system (GPS) device **1513**, compass **1514**, a chipset **1506**, an antenna **1516**, a power amplifier **1509**, a touchscreen controller **1511**, a touchscreen display **1517**, a speaker **1515**, a camera **1503**, and a battery **1518**, as illustrated, and other components such as a digital signal processor, a crypto processor, an audio codec, a video codec, an accelerometer, a gyroscope, and a mass storage device (such as hard disk drive, solid state drive (SSD), compact disk (CD), digital versatile disk (DVD), and so forth), or the like. In further embodiments, any component housed within computing device **1500** and discussed above may contain a stand-alone integrated circuit memory die that includes one or more arrays of NVM devices.

(156) In various implementations, the computing device **1500** may be a laptop, a netbook, a notebook, an Ultrabook, a smartphone, a tablet, a personal digital assistant (PDA), an ultra-mobile PC, a mobile phone, a desktop computer, a server, a printer, a scanner, a monitor, a set-top box, an entertainment control unit, a digital camera, a portable music player, or a digital video recorder. In further implementations, the computing device **1500** may be any other electronic device that processes data.

(157) FIG. 16 illustrates an integrated circuit (IC) structure **1600** that includes one or more embodiments of the disclosure. The integrated circuit (IC) structure **1600** is an intervening substrate used to bridge a first substrate **1602** to a second substrate **1604**. The first substrate **1602** may be, for instance, an integrated circuit die. The second substrate **1604** may be, for instance, a memory module, a computer mother, or another integrated circuit die. Generally, the purpose of an integrated circuit (IC) structure **1600** is to spread a connection to a wider pitch or to reroute a connection to a different connection. For example, an integrated circuit (IC) structure **1600** may couple an integrated circuit die to a ball grid array (BGA) **1607** that can subsequently be coupled to the second substrate **1604**. In some embodiments, the first substrate **1602** and the second substrate **1604** are attached to opposing sides of the integrated circuit (IC) structure **1600**. In other embodiments, the first substrate **1602** and the second substrate **1604** are attached to the same side of the integrated circuit (IC) structure **1600**. And in further embodiments, three or more substrates are interconnected by way of the integrated circuit (IC) structure **1600**.

(158) The integrated circuit (IC) structure **1600** may be formed of an epoxy resin, a fiberglass-reinforced epoxy resin, a ceramic material, or a polymer material such as polyimide. In further implementations, the integrated circuit (IC) structure may be formed of alternate rigid or flexible materials that may include the same materials described above for use in a semiconductor substrate, such as silicon, germanium, and other group III-V and group IV materials.

(159) The integrated circuit (IC) structure may include metal interconnects **1608** and vias **1610**, including but not limited to through-silicon vias (TSVs) **1612**. The integrated circuit (IC) structure **1600** may further include embedded devices **1614**, including both passive and active devices. Such embedded devices **1614** include capacitors, decoupling capacitors, resistors, inductors, fuses, diodes, transformers, device structure including transistors, such as TMD nanosheet transistors **100**, **200**, or transistor arrays **250** or **260** described in association with FIGS. 1A, 2A, 2C and 2D. Referring again to FIG. 16 the integrated circuit (IC) structure **1600** may further include embedded devices **1614** such as one or more resistive random-access devices, sensors, and electrostatic discharge (ESD) devices. More complex devices such as radiofrequency (RF) devices, power amplifiers, power management devices, antennas, arrays, sensors, and MEMS devices may also be formed on the integrated circuit (IC) structure **1600**.

(160) Thus, one or more embodiments of the present disclosure relate to encapsulation layer for TMD nanosheet transistors **100**, **200**, or transistor arrays **250** or **260**, as described above.

(161) In a first example, a transistor includes a channel layer including a transition metal dichalcogenide (TMD) material, an encapsulation layer on a first portion of the channel layer, a gate electrode above the encapsulation layer, a gate dielectric layer between the gate electrode and the encapsulation layer, a source contact on a second portion of the channel layer and a drain contact on a third portion of the channel layer, where the gate structure is between the drain contact and the source contact.

(162) In second examples, for any of first example, the TMD material includes at least one of molybdenum, tungsten, titanium or chromium, and at least one of sulfur, selenium or tellurium.

(163) In third examples, for any of the first through second examples, the channel layer has a thickness between 1 and 4 monolayers.

(164) In fourth examples, for any of the first through third examples, the encapsulation layer includes oxygen and at least one of aluminum, molybdenum or tungsten, or a sub-stoichiometric aluminum oxide, tungsten oxide, or molybdenum oxide.

(165) In fifth examples, for any of the first through fourth examples, the encapsulation layer includes a first metal and the TMD material includes a second metal, the second metal different from the first metal.

(166) In sixth examples, for any of the first through fifth examples, the encapsulation layer includes a material that is different from a material of the gate dielectric layer.

(167) In seventh examples, for any of the first through sixth examples, the channel layer is a first

channel layer, where the drain contact is a first drain contact, where the source contact is a first source contact, where in the gate electrode is a first gate electrode, where the gate dielectric layer is a first gate dielectric layer and where the transistor is a first transistor in an array of transistors, where the array of transistors further includes a second transistor. The second transistor includes a second channel layer including the TMD material, a second gate electrode above a fourth portion of the second channel layer, a second gate dielectric layer between the second gate electrode and the second channel layer, a second source contact on a fifth portion of the second channel layer and a second drain contact on a sixth portion of the second channel layer, where the second gate electrode is between second drain contact and the second source contact.

(168) In eighth examples, for any of the first through seventh examples, the encapsulation layer is a first encapsulation layer, and the second transistor further includes a second encapsulation layer, where the first encapsulation layer includes a first material, and the second encapsulation layer includes a second material.

(169) In ninth examples, for any of the first through eighth examples, the first encapsulation layer includes one of oxygen and aluminum, or sub-stoichiometric aluminum oxide, and the second encapsulation layer includes oxygen and molybdenum or tungsten, or sub-stoichiometric tungsten oxide or molybdenum oxide.

(170) In tenth examples, for any of the first through ninth examples, the first gate dielectric and the second gate dielectric layer include a same or a different material and the first and the second gate electrode include a same or a different material.

(171) In eleventh examples, transistor includes a first channel layer over a second channel layer, where the first and the second channel layers each include a monocrystalline transition metal dichalcogenide (TMD) material, the TMD material including a first metal, an encapsulation layer including a second metal, where the encapsulation layer is adjacent the first channel layer and the second channel layer. The transistor further includes a source structure coupled to a first end of the first and second channel layers, a drain structure coupled to a second end of the first and second channel layers, a gate electrode between the source material and the drain material, and between the first channel layer and the second channel layer and a gate dielectric between the gate electrode and the encapsulation layer.

(172) In twelfth examples, for any of the eleventh examples, the first metal comprises molybdenum, tungsten or chromium, wherein the TMD material further includes at least one of sulfur, selenium or tellurium and wherein the first and second channel layers each have a thickness between 1 and 4 monolayers.

(173) In thirteenth examples, for any of the eleventh through twelfth examples, the second metal includes aluminum, tungsten, molybdenum, and encapsulation layer includes a thickness between 0.5 nm and 3 nm.

(174) In a fourteenth example, for any of the eleventh through thirteenth examples, the first metal is different from the second metal.

(175) In fifteenth examples, for any of the eleventh through fourteenth examples, each of the first and second channel layers have a first thickness along a first direction orthogonal to a length of the first and of the second channel layers, where each of the first and second channel layers have a second thickness along a second direction orthogonal to the first direction and to the length, where the first thickness is between 5 nm and 60 nm, and where the second thickness is between 1 and 4 monolayers, and where the encapsulation layer clads each of the first and the second channel layers in the first and in the second directions.

(176) In sixteenth examples, a method of fabricating a transistor includes patterning a material layer stack including a layer of a III-N material on a plurality of bilayers, where each bilayer is formed by depositing a channel layer including a monocrystalline transition metal dichalcogenide (TMD) on a layer of the III-N material. The method further includes forming a dielectric adjacent the dummy gate and adjacent to the block and etching and removing a portion of the dielectric to



form an exposed portion of the block. The method further includes etching and removing the layer of III-N material in each bilayer to suspend a plurality of channel layers in the exposed portion of the block and forming a liner to clad the plurality of channel layers in the exposed portion of the block. The method further includes forming a gate between each of plurality of channel layers in a first portion of the exposed portion of the block and forming a first contact in a second portion of the block and a second contact in a third portion of the block, where the first portion is between the second portion and the third portion.

(177) In seventeenth examples, for any of the sixteenth example, forming the gate structure includes forming a dummy gate after formation of the liner, forming a dielectric layer adjacent to the dummy gate and removing the dummy gate to deposit a material of the gate structure.

(178) In eighteenth examples, for any of the sixteenth through seventeenth examples, forming the gate structure includes conformally depositing a gate oxide on the liner and depositing a gate electrode material adjacent to the gate dielectric layer.

(179) In nineteenth examples, for any of the sixteenth through eighteenth examples, etching and removing the layer of III-N material adjacent to the channel layer to form a plurality of channel layers in the exposed portion of the block includes anchoring opposite ends of the block to the dielectric.

(180) In twentieth example, for any of the sixteenth through nineteenth examples, forming the source and drain contact includes etching a portion of the liner from an upper surface of an uppermost channel layer in the plurality of channel layers.

## Claims

1. An apparatus, comprising: a first transistor of a first conductivity type, the first transistor comprising: a first channel region comprising a transition metal and a chalcogen; a first gate electrode coupled to the first channel region; an encapsulation material in direct contact with the first channel region, wherein the encapsulation material comprises oxygen and a second metal, different than the transition metal; a first gate insulator between the first gate electrode and the encapsulation material, wherein the first gate insulator is in direct contact with the encapsulation material; and a first source contact and a first drain contact coupled to the first channel region, wherein the first gate electrode and the encapsulation material are between the first drain contact and the first source contact; a second transistor of a complementary second conductivity type and laterally adjacent to the first transistor, the second transistor comprising: a second channel region comprising the transition metal and the chalcogen, but not in direct contact with the encapsulation material; a second gate electrode coupled to the second channel region; a second gate insulator between the second gate electrode and the second channel region; and a second source contact and a second drain contact coupled to the second channel region, wherein the second gate electrode is between the second drain contact and the second source contact.
2. The apparatus of claim 1, wherein the first conductivity type is n-type and the second conductivity type is p-type.
3. The apparatus of claim 1, wherein: the first channel region is over a third channel region, wherein the first and the third channel regions each comprise the transition metal and the chalcogen; and the encapsulation layer is in direct contact with the first channel region and in direct contact with the third channel region.
4. The apparatus of claim 3, wherein the transition metal comprises molybdenum, tungsten or chromium, wherein the chalcogen comprises sulfur, selenium or tellurium and wherein the first and third channel regions each have a thickness between 1 and 4 monolayers.
5. The apparatus of claim 3, wherein the second metal comprises aluminum, tungsten, or molybdenum, and the encapsulation layer has a thickness between 0.5 nm and 3 nm.
6. The apparatus of claim 3, wherein each of the first and third channel regions has a first thickness

along a first direction orthogonal to a length of the first and second channel regions, wherein each of the first and second channel regions have a second thickness along a second direction orthogonal to the first direction and orthogonal to the length, wherein the first thickness is between 5 nm and 60 nm, and wherein the second thickness is between 1 and 4 monolayers, and wherein the encapsulation layer clads each of the first and the second channel regions in the first and in the second directions.

7. The apparatus of claim 1, wherein: the second metal is aluminum; the second transistor comprises a second encapsulation material in direct contact with the second channel region and in direct contact with the second gate insulator; and the second encapsulation material comprises oxygen and molybdenum or tungsten.

8. The apparatus of claim 1, wherein the gate insulator comprises a third metal, different from the second metal.

9. The apparatus of claim 1, wherein the transition metal comprises at least one of molybdenum, tungsten, titanium or chromium, and the chalcogen comprises sulfur, selenium or tellurium.

10. The apparatus of claim 1, wherein the first channel region has a thickness between 1 and 4 monolayers.

11. The apparatus of claim 1, wherein the encapsulation layer comprises a sub-stoichiometric aluminum oxide, tungsten oxide, or molybdenum oxide.

12. The apparatus of claim 1, wherein the first gate insulator and the second gate insulator comprise a same material.

13. The apparatus of claim 1, wherein the second gate insulator is in direct contact with the second channel region.

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